

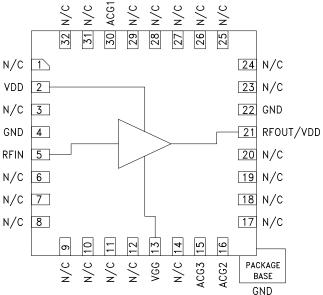
ROHS V

Typical Applications

The HMC1049LP5E is ideal for:

- Test Instrumentation
- High Linearity Microwave Radios
- VSAT & SATCOM
- Military & Space

Functional Diagram



HMC1049LP5E

GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 0.3 - 20 GHz

Features

Noise Figure: 1.8 dB P1dB Output Power: +14.5 dBm Psat Output Power: +17.5 dBm High Gain: 15 dB Output IP3: +29 dBm Supply Voltage: Vdd = +7V @ 70 mA 50 Ohm Matched Input/Output 32 Lead 5x5 mm SMT Package: 25mm²

General Description

The HMC1049LP5E is a GaAs MMIC Low Noise Amplifier which operates between 0.3 and 20 GHz. This LNA provides 15 dB of small signal gain, 1.8 dB noise figure, and output IP3 of 29 dBm, while requiring only 70 mA from a +7 V supply. The P1dB output power of 14.5 dBm enables the LNA to function as a LO driver for balanced, I/Q or image reject mixers. Vdd can be applied to pin 2 or pin 21. Pin 21 will require a bias tee. The HMC1049LP5E amplifier I/Os are internally matched to 50 Ohms and the device is supplied in a compact, leadless QFN 5x5 mm surface mount package.

Electrical Specifications, $T_A = +25^\circ$ C, Vdd = +7V, Idd = 70 mA^[1]

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Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range		0.3 - 1			1 - 14			14 - 20		GHz
Gain	13.5	16.5		12	15		10	13		dB
Gain Variation Over Temperature		0.006			0.019			0.017		dB/°C
Noise Figure		2.5	3.5		1.8	2.5		2.7	4.0	dB
Input Return Loss		15			13			14		dB
Output Return Loss		8			15			13		dB
Output Power for 1 dB Compression (P1dB)		15			14.5			13		dBm
Saturated Output Power (Psat)		18			17.5			16		dBm
Output Third Order Intercept (IP3) [2]		31			29			26		dBm
Total Supply Current		70			70			70		mA

[1] Adjust Vgg between -2 to 0V to achieve Idd = 70 mA typical.

[2] Measurement taken at Pout / tone = +8 dBm.

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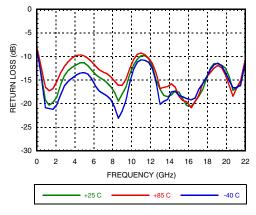
Data taken with Vdd applied to pin 2.



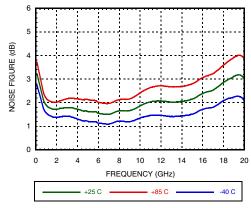
GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 0.3 - 20 GHz

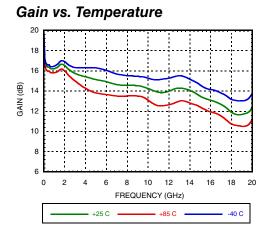
Broadband Gain & Return Loss 20 15 10 (qB) 5 RESPONSE 0 -5 -10 -15 -20 -25 12 16 18 20 22 24 0 2 4 6 8 10 14 FREQUENCY (GHz) S21 S11 S22

Input Return Loss vs. Temperature

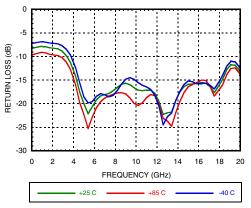


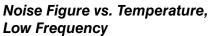
Noise Figure vs. Temperature

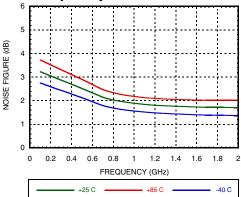




Output Return Loss vs. Temperature







AMPLIFIERS - LOW NOISE - SMT

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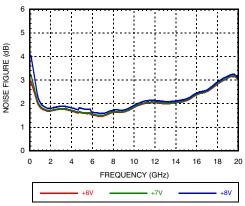
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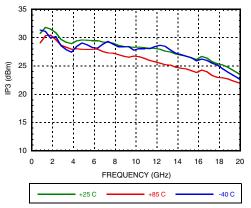
GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 0.3 - 20 GHz

Data taken with Vdd applied to pin 2.

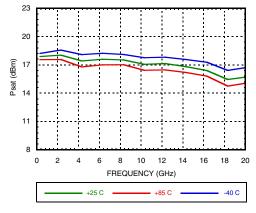
Noise Figure vs. Vdd

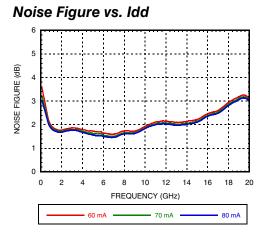


Output IP3 vs. Temperature

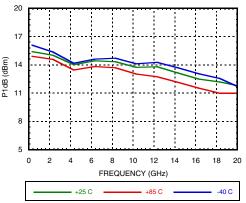


Psat vs. Temperature

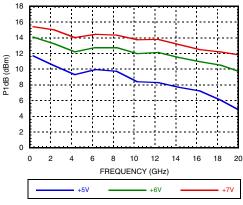




P1dB vs. Temperature







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20 22

-40 C

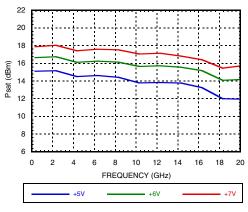
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Data taken with Vdd applied to pin 2.

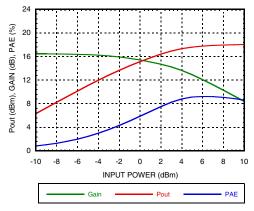


GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 0.3 - 20 GHz

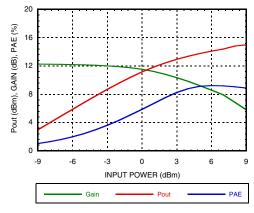
Psat vs. Vdd



Power Compression @ 2 GHz



Power Compression @ 18 GHz



Reverse Isolation vs. Temperature

FREQUENCY (GHz)

+85 C



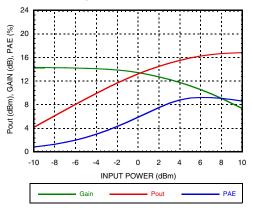
6 8 10 12 14 16 18

+25 C

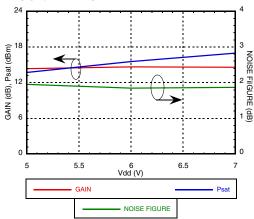
4

2

0



Noise Figure, Gain & Power vs. Supply Voltage @ 12 GHz



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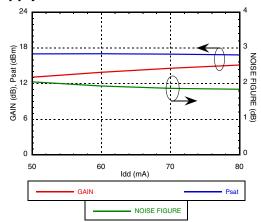
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GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 0.3 - 20 GHz

Data taken with Vdd applied to pin 2.

Noise Figure, Gain & Power vs. Supply Current @ 12 GHz

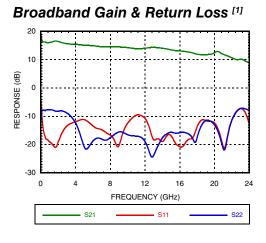




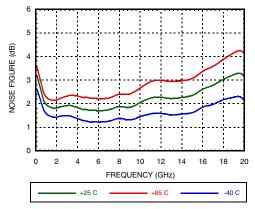
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GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 0.3 - 20 GHz

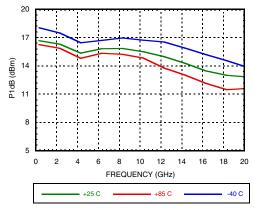
Data taken with Vdd applied to bias tee at pin 21.



Noise Figure vs. Temperature [1]



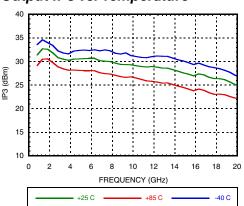




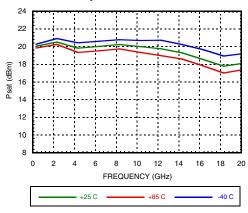
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[1] Vdd= +4V, supply to bias tee.

20 18 16 (dB) 14 GAIN 12 10 8 12 20 2 4 6 8 10 14 16 18 0 FREQUENCY (GHz) -40 C +25 C +85 C



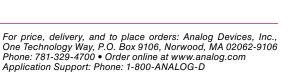
Psat vs. Temperature [1]



Gain vs. Temperature [1]

Output IP3 vs. Temperature [1]

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GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 0.3 - 20 GHz

Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	+10V
Drain Bias Voltage (RF out / Vdd)	+7V
RF Input Power	+18 dBm
Gate Bias Voltage, Vgg1	-2V to +0.2V
Channel Temperature	175 °C
Continuous Pdiss (T = 85 °C) (derate 37.1 mW/°C above 85 °C)	3.34 W
Thermal Resistance (Channel to die bottom)	26.9 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A

Typical Supply Current vs. Vdd

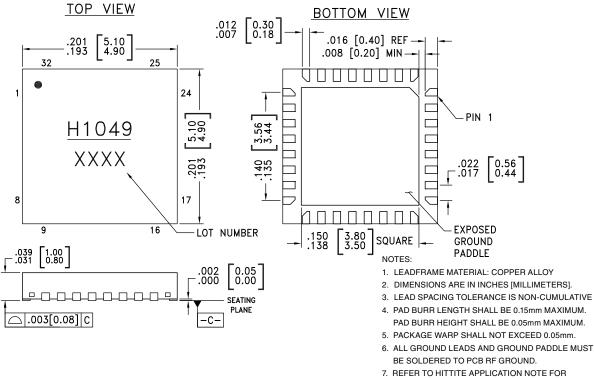
Vdd (V)	ldd (mA)
+5	70
+6	70
+7	70

Adjust Vgg1 to achieve Idd = 70 mA



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

Outline Drawing



7. REFER TO HITTITE APPLICATION NOTE F SUGGESTED PCB LAND PATTERN.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating ^[2]	Package Marking ^[1]	
HMC1049LP5E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1	<u>H1049</u> XXXX	

[1] 4-Digit lot number XXXX

[2] Max peak reflow temperature of 260 °C

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Pin Descriptions

Pad Number	Function	Description	Interface Schematic
1, 3, 6-12, 14, 17-20, 23-29, 31, 32	N/C	No connection required. The pins are not connected inter- nally; however, all data shown herein was measured with these pins connected to RF/DC ground externally.	
2	Vdd	Power supply voltage for the amplifier. External bypass capacitors 100 pF, and 0.01 uF are required.	∩Vdd ↓↓ ↓
4, 22	GND	These pins and the exposed ground paddle must be con- nected to RF/DC ground.	
5	RFIN	This pin is DC coupled and matched to 50 Ohms.	RFIN ACG2
13	Vgg	Gate control for amplifier. External bypass capacitors 100 pF, 0.01uF, and 4.7 uF are required. Adjust voltage to achieve typical Idd.	Vgg O
15, 16	ACG3, ACG2	Low frequency termination. External bypass capacitors 100 pF are required.	RFIN ACG2
21	RFOUT/Vdd	This pin is DC coupled and matched to 50 Ohms.	O RFOUT
30	ACG1	Low frequency termination. External bypass capacitor 100 pF required.	ACG1 RFOUT

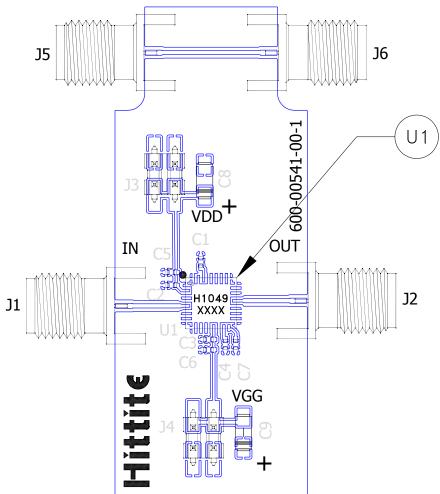
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List of Materials for Evaluation PCB EV1HMC1049LP5 [1]

Item	Description
J1, J2, J5, J6	PCB Mount SMA RF Connector.
J3, J4	DC Pins.
C1 - C4	100 pF Capacitor, 0402 Pkg.
C5 - C7	10000 pF Capacitor, 0402 Pkg.
C8 - C9	4.7 uF Capacitor, Tantalum.
U1	HMC1049LP5E.
PCB ^[1]	600-00541-00-1 Evaluation PCB.

[1] Circuit Board Material: Rogers 4350 or Arlon 25FR

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.

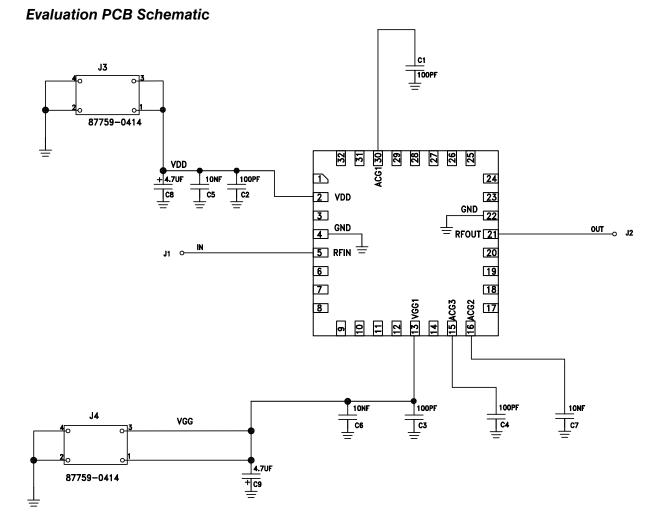
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